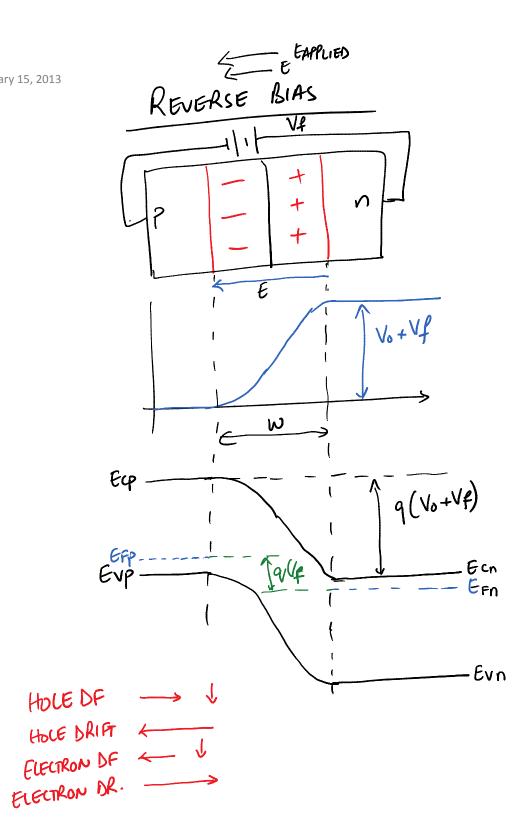


FORWARD BIAS (FB)

- THE ELECTROSTATIC POTENTIAL BARRIER AT THE JUNCTION IS LOWERED BY Uf FROM VO * : VF IS IN OPPOSITE POLARITY AS VO
- E FIELD GOES DOWN: APPLIED E 15 IN OPPOSITE DIRECTION AS INBUILT E X
- DIFF USION CURRENT INCREASES -: OF INJECTION OF CARRIERS (MAJORITY) IN THE P ANDA * REGIONS. SINCE THE BARRIER IS LOWERED, MAJORITY CARRIERS HAVE SUFFICIENT ENERGY TO CAUSE AN INCREASE IN CURRENT!
- DRIFT CURRENT REMAINS THE SAME -: IT DEPENDS ONLY ON EHP GENERATION OF X MINORITY CARRIERS IN THE MAJORITY REGIONS



SOME USEFUL APPLICATION WHERE

EHP GENERATION IS INCREASED, LEADING

TO DRIPT CURRENT INCREASE, OTHER THAN

THERMAL EXCITATION IS DPICAL EXCITATION ->

PHOTO DIODE

W=
$$\left[\frac{2.66 \text{ (Vo-Vf)}}{9}\left(\frac{\text{(Nap)eff}+(\text{Ndn}^{\dagger})\text{eff}}{\text{(Nap)eff}}\right)\right]^{\frac{1}{2}}$$

REVERSE BIAS

- * APPLIED & FIELD IS NOW IN THE DIRECTION OF INTERNAL E FIELD !. NET E FIELD INCREASES
- W INCREASES -> LARGE BARRIER *
- MAJORITY CARRIERS DON'T HAVE THE EVERGY TO PAGE THE BARRIER : DIFFUSION CURRENT X DELLEAGES
- DRIFT CURRENT REMAINS THE SAME .: IT DEPENDS ON EHP GENERATION OF MINORITY * CALRIERS DUE TO THERMAL EXCITATION!